impurity into the polycrystalline silicon in the formation of a source and a drain of the NMOS and PMOS. In this case, as to the P+resistor 116, boron or BF_2 is used as the impurity with a concentration of approximately 1 x 10^{19} atoms/cm^3 or more, a sheet resistance value of approximately several hundred Ω/square to 1 kΩ/square, and a temperature coefficient of approximately several hundred ppm/°C to 1000 ppm/°C. As to the N+resistor 117, phosphorous or arsenic is used as the impurity with a concentration of approximately 1 x 10^{19} atoms/cm^3 or more, a sheet resistance value of approximately one hundred Ω/square to several hundred Ω/square, and a temperature coefficient of approximately several hundred ppm/°C to 1000 ppm/°C. Further, Fig. 2 shows both the N+resistor 117 and the P+resistor 116. However, one of these resistors may constitute the semiconductor device for the purpose of reducing the number of steps and cost in consideration of the characteristics required for the semiconductor device and characteristics of the resistors.--

C1

Please replace the paragraph beginning at page 136, line 6, with the following rewritten paragraph:

C2

--Next, as shown in Fig. 55, the thin film polycrystalline silicon 136 is patterned by the photolithography method and etching to form a resistor.--.